

Layer	Theoretical calculation (nm)	Experimental (nm)	% Error	Linewidths (photoresist) (nm)	Linewidths (after PR Strip) (nm)	% Overetch
Field Oxide	505.8	477.2	5.65	?	3000	?
Polysilicon	?	?	?	?	?	?
Gate Oxide	80.1	86.5	7.40	3628	4000	?
Intermed Oxide	386.3	320	17.2	?	?	?
Aluminum	?	?	?	2088	2520	?